

# UNIT-IV

Date: \_\_\_ / \_\_\_ / \_\_\_

MON TUE WED THU FRI SAT SUN

Subject

## OPTICAL SOURCES

- \* LED } Construction, operating Principle
- \* LASER } and characteristics of their light
- \* ILD - Injection Laser Diodes.

Light source should have following characteristics (प्रकार, गुण, उपयोग)

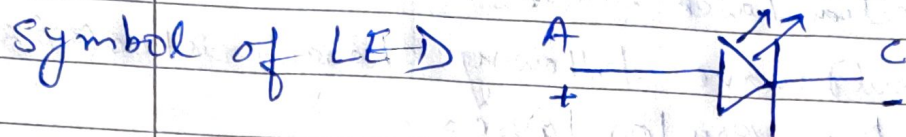
- \* optical light has very low losses
- \* optical light o/p must be stable under different conditions
- \* o/p light should be highly directional
- \* o/p light should be modulated easily i.e. by  $V$  or by  $I$
- \* o/p light has small bandwidth and less dispersion
- \* Size of source should be comparable to optical fiber
- \* Long life, coherence, Reliability

### Imp Facts

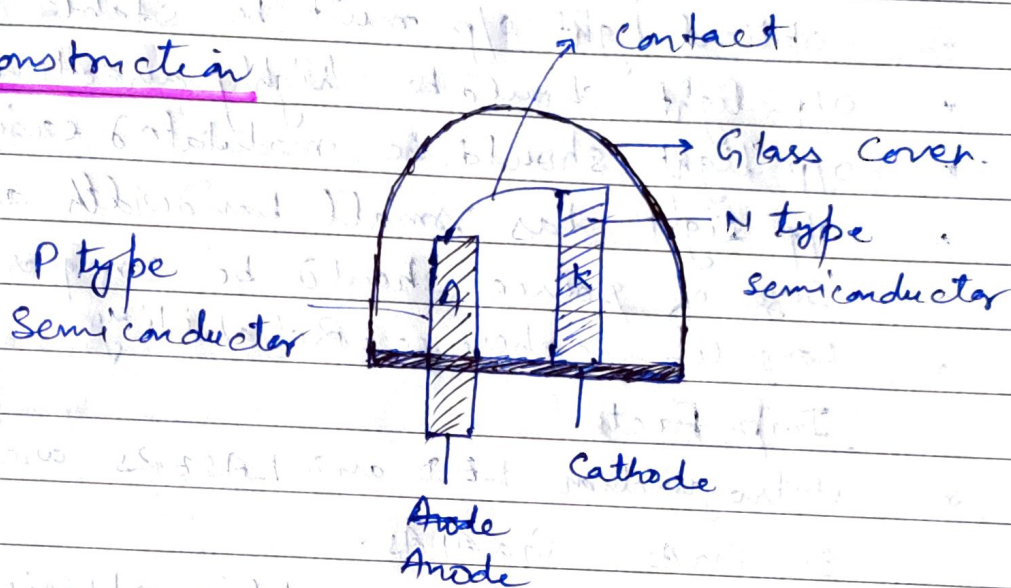
- \* Heterojunction LED and LASERS are mostly used  
Ex GaAs, GaAlAs.
- \* Source to fiber coupling efficiency depends upon size, angle, alignment, N.A., of optical source-light
- \* Si & Ge is not used for LED.
- \* LED is used as optical source for short distance
- \* LASER is used for long distance.
- \* Direct band gap materials are preferred for Laser Diodes.

## LED - Light Emitting Diodes

- \* It converts electrical signal to light signal.



### Basic LED construction



- \* LED एक PN junction होता है जो कि forward Biase होता है
- \* यह PN junction GaAs, GaAsP, GaP का बना होता है। Si तथा Ge का प्रयोग LED में नहीं किया जाता है। Si तथा Ge प्रकाश के स्थान पर Heat generate करते हैं
- \* It has heavily doped P-N junction
- \* LED junction is made such that emitted light should be in visible region ( $\lambda$  700nm to 380nm)  $E = hc/\lambda$
- \* For LED threshold voltage is higher (1.83 to 3.6) It is differ as per o/p colour light

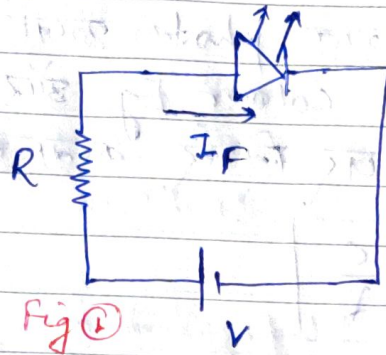


Fig 1

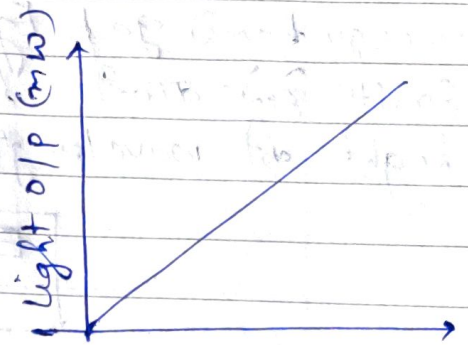


Fig 2 Forward Voltage & Current

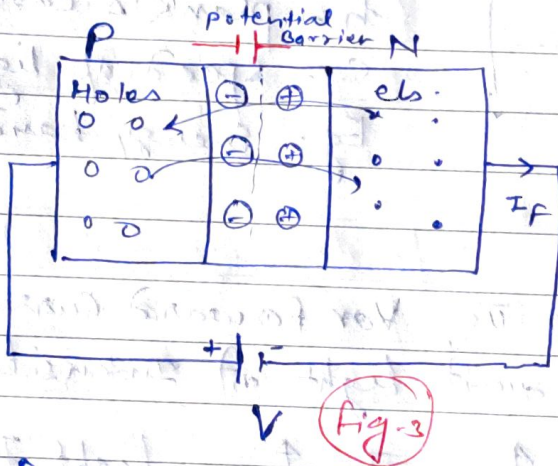


Fig 3

as  $V \uparrow$   
 as  $V \uparrow$   $I_F \uparrow$   
 light Intensity  $\uparrow$

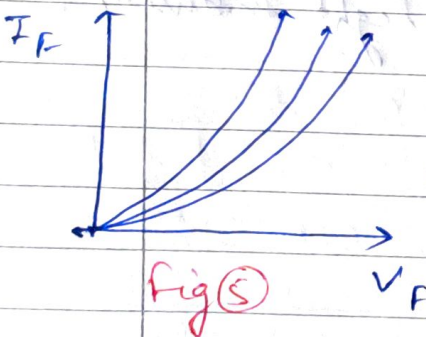


Fig 5

curve is different for different colour

$$E = \frac{hc}{\lambda}$$

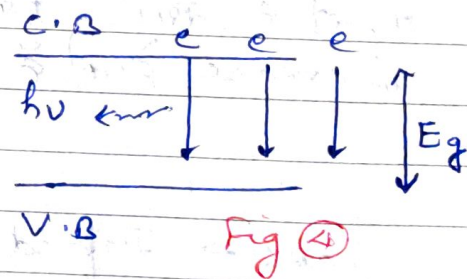


Fig 4

Working Principle of LED . जब किसी GaAs, GaAsP

के PN junction को forward biased किया जाता है तो P type के holes और N type के els एक दूसरे की तरफ attract होकर recombine हो जाते हैं। recombination पर els और holes vanish (निलुप्त) हो जाते हैं। तथा light emit करते हैं। els जो कि higher Band C.B से निचले Band V.B के holes पर जाते हैं

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energy band gap  $E_g$  के संगत photon ऊर्जा emit करता है।  
 Emit होने वाली light का colour  $E_g$  और निकलने वाली  
 light की wavelength ( $\lambda$ ) पर निर्भर करता है।

$$E_g = \frac{hc}{\lambda}$$

$$\lambda = \frac{hc}{E_g}$$

$h$  = plank's const.

$c$  = speed of light

$E_g$  = Energy band gap

Forward Voltage  $V_f$  बढ़ने पर, Forward Current  $I_f$   
 बढ़ती है तथा Emit होने वाली light की Intensity भी  
 increase होती है।

$V_f \uparrow \quad I_f \uparrow \quad \text{light Intensity} \uparrow$

GaAs  $\rightarrow$  Infrad Region (IR)

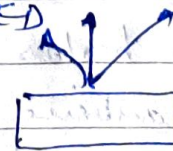
GaAs, Px  $\rightarrow$  For different colour

## Types of LED

① Edge LED



② Surface LED



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## LED की विशेषताएँ

- ① Durable
- ② Small size
- ③ Easy fabrication
- ④ Less costly
- ⑤ Driven ckt is simple
- ⑥ Silent operation
- ⑦ low power consumption
- ⑧ Long life
- ⑨ less heating effect

Application → 7 Segment Display

In optical source

As Indicator

As light source

LED TV.

Subject

# LASER :

- \* Introduction
- \* Absorption, Spontaneous, & Stimulated Emission
- \* Ruby laser, He+Ne laser
- \* Semiconductor Injection Laser.
- \* Population Inversion
- \* Maser (Full form and Introduction)
- \* Properties of LASER and Application

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\* MASER - Microwave Amplification by Stimulated Emission of Radiation - First Maser - 1954

It is just like LASER but rays or signal is in Microwave Invisible format

\* LASER : "Light Amplification by Stimulated Emission of Radiation"

First LASER - 1960 (Ruby LASER)

Introduction → LASER is a coherent, monochromatic, unidirectional, intense optical light source. It works on Stimulated Emission of Radiation

Properties of LASER light → \* Monochromatic (एकवर्णी)

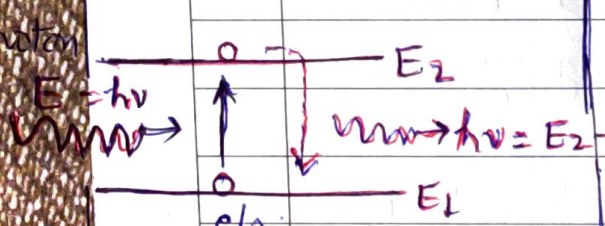
- \* Narrow and parallel ray beam (समानक या संकीर्ण)
- \* High Intensity light (can produce  $10^4$ °c temp.)
- \* Unidirectional (एकदिशीय)
- \* Coherent ray (कमल होकर)
- \* Do not spread



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	<u>Types of LASER</u>			
				Ruby Laser
				He-Ne Laser
				Semiconductor Laser

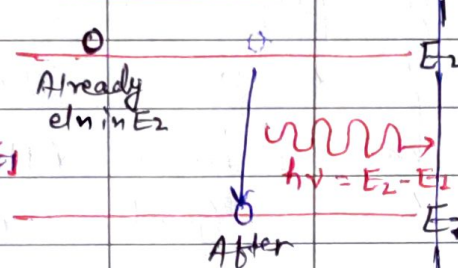
First we study these basic operation in LASER action

Absorption of photon



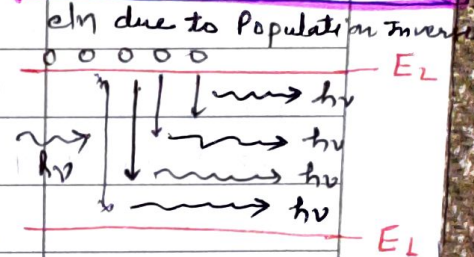
absorption of a photon will occur when the quantum energy of the photon precisely matches the energy gap ( $E_2 - E_1$ )  
 e- absorbs photon energy Goes to  $E_2$  Energy level  
 life time in excited state  $E_2$  is less. e- jumps back to  $E_1$  and emits  
 Corresponds energy in form of photon  $E = hv = E_2 - E_1$

Spontaneous Emission



e- may already in  $E_2$  energy level with excited state for very short time i.e.  $10^{-8}$  s  
 After  $10^{-8}$  s time this e- jumps to energy level  $E_1$  and releasing Random Energy photon  
 $E_p = E_2 - E_1$   
 All such transition give rise to emission of photon which are out of phase

Stimulated Emission



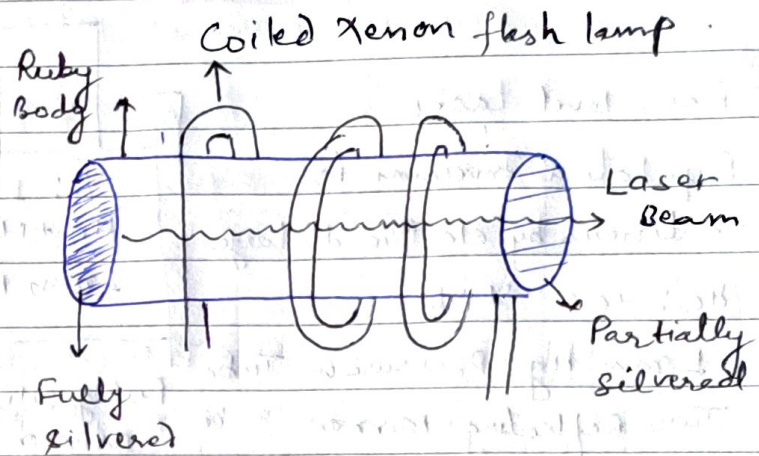
e- are already in  $E_2$  state by population inversion  
 External Photon Stimulate  $E_2$  energy level e- to jump back to  $E_1$  and releasing new photons.  
 All such photon emitted has same polarization, phase, direction and are coherent.  
 so Intense light ray occur at o/p. This is laser operation.



Subject

## Ruby LASER →

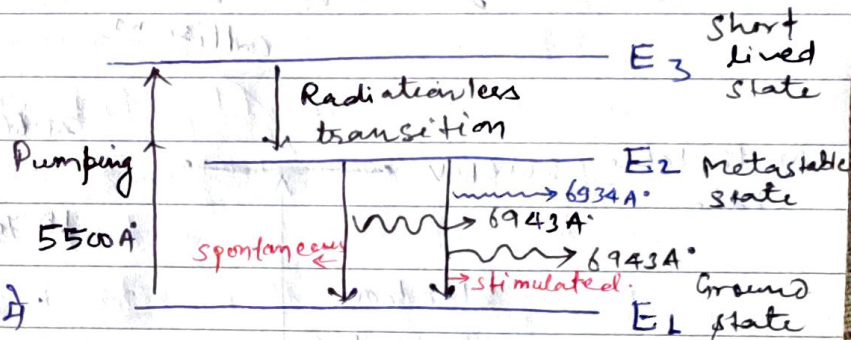
- \* First Laser - 1960. Ruby laser
- \* It is solid state laser
- \* It is three state laser.



Working → Ruby Body is made of  $Al_2O_3 + 0.05\% Cr_2O_3$  crystal. इसका colour गुलाबी होता है।

जब Xenon flash lamp के द्वारा  $1ms$  तक flash दी जाती है तो  $5500\text{\AA}$  के Radiation Cr ions के द्वारा absorb कर लिए जाते हैं।

अतः इनकी pumping  $E_3$  अवस्था में हो जाती है। यहाँ इनका (Cr ions का) life time  $10^0 s$  होता है अतः



यहाँ  $E_2$  अवस्था में आ जाते हैं। यहाँ इनका life time  $10^3 s$  होता है।  $E_2$  energy level में आयत की सख्या बढ़ती जाती है इसे population Inversion कहते हैं।  $E_2$  level से कोई भी आयत spontaneously  $E_1$  level पर आता है। और यह आयत Ruby crystal body के silvered part से टकराकर ऊपर आयतों को  $E_2$  level से stimulate करता है। यह क्रिया बार-बार होती है जिस कारण crystal के अन्दर उत्पन्न होने वाले stimulated ions crystal की faces से टकराकर Intense photon ray के रूप में partially silvered face से बाहर laser ray की form में आते हैं।

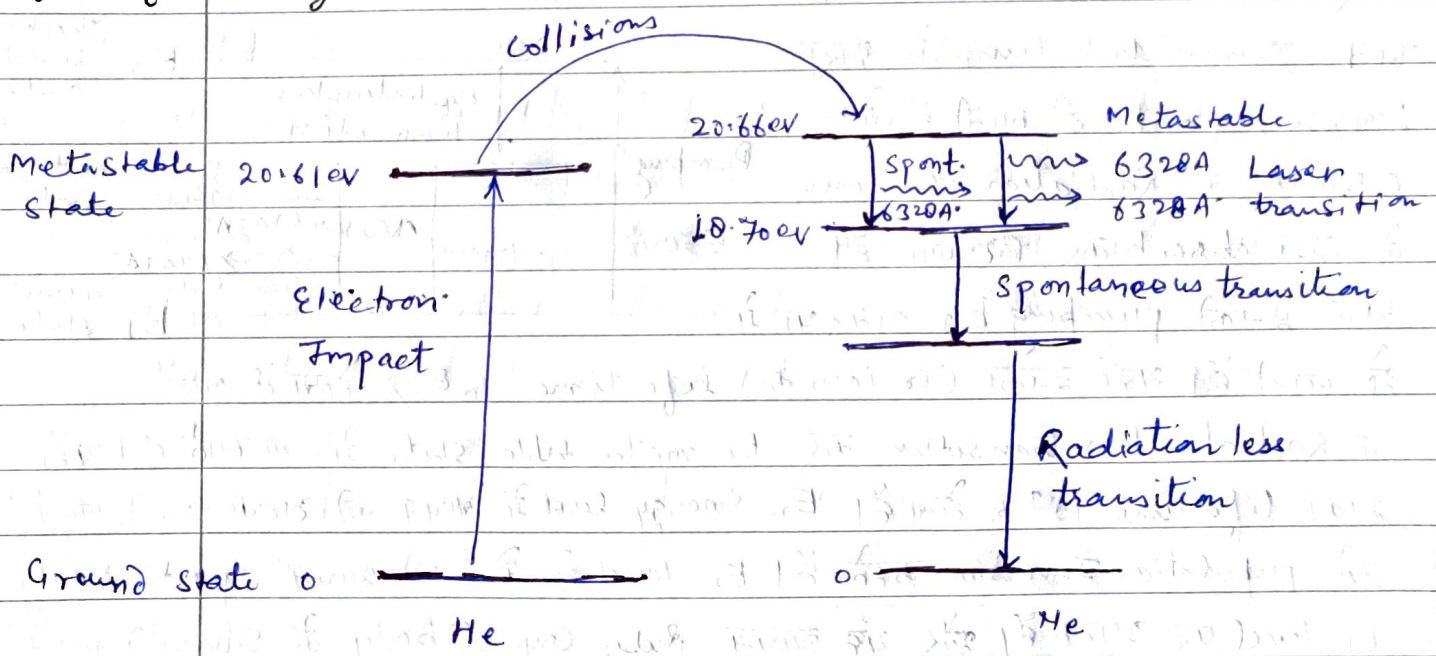
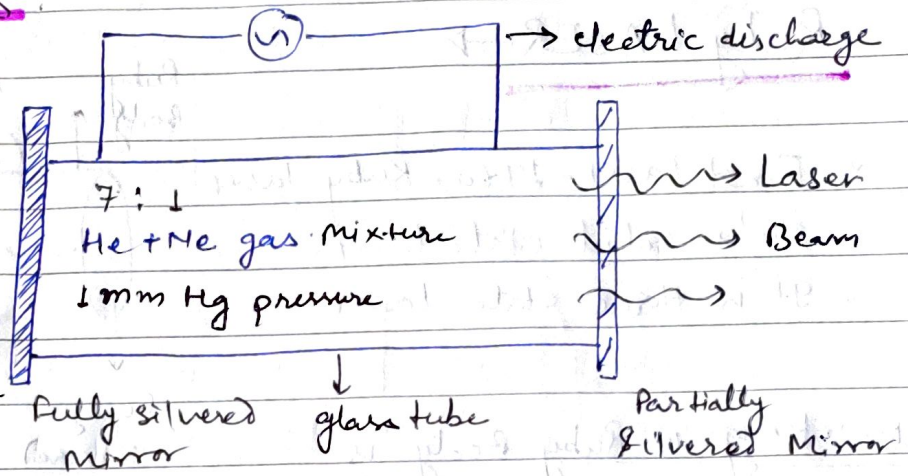
### Disadvantages of Ruby LASER

- \* It requires high pumping power.
- \* Some energy of  $6943\text{\AA}$  is absorb by  $E_1$  state ions.
- \* ये कमिया He-Ne Laser में दूर करी जाती

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Helium-Neon LASER

- \* Four level Laser
- \* Population Inversion is continuous by electric discharge
- \* He:Ne = 7:1
- \* 1 mm Hg Pressure in Tube
- \* Two Reflecting Mirrors
- \* Spacing between Mirror is multiple of  $\lambda$  of laser light



A Four level LASER

- \* He and Ne gas mix. is electrically pumped to Metastable level.
- \* Ne ions are populated Inversion by kinetic energy of He ions.
- \* Excited Ne atom jumps to 10.70 eV level and spontaneously and emits light 6328A photon. यह photon mirror से तब तक टकराता है जब तक यह Stimulated Emission के द्वारा अन्य Inphase photon (6328A) न निकाल दे। यह process लगातार चलती है और light ray strong Intensity की हो जाती है जो वह Laser Beam के रूप में partially silvered face से निकलती है।

\* He atom 18.7 eV level से Spont. transition के द्वारा Metastable state में शीत है और कि Radiationless transition के द्वारा Ground level पर पहुँच जाता है।

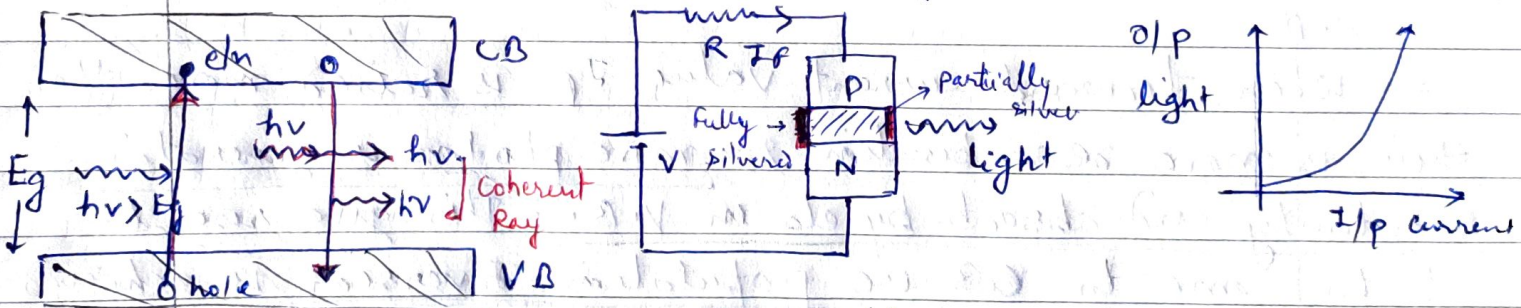
Advantage → \* Last transition is Radiationless so no absorption by ground level atoms.

\* He-Ne laser Beam is continuous as electric discharge is continuous process. (Ruby laser - Flash lamp)

\* It needs less excitation power.

Semiconductor Injection LASER Diode (ILD)

\* First ILD - Ga-As \*  $E_g$  in eV (Energy Band Gap)



Absorption      Stimulated Emission

PN Middle region is work as resonator as its one side is fully silvered and other side partially silvered.

Working: Ga-As का PN junction को की Forward Biased में प्रयोग किया जाता है इसमें P तथा N type highly doped होते हैं जैसे ही PN junction of forward Biased किया जाता है तो forward current  $I_f$  बहने लगती है तथा  $e^-$  और holes का recombination होता है,  $I_f$  का मान अधिक

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होने पर C.B में el's की संख्या बढ़ती जाती है।

तथा  $I_F$  के अधिक मान के लिए population inversion प्राप्त हो जाती है।

population inversion से पहले ही क्वि Spontaneous Emission होती है।

population inversion के बाद el's और hole के recombination से उत्पन्न photon Stimulated Emission किता करता है तथा उत्पन्न होने वाले photon, same phase में होकर laser o/p देते हैं।

steps में इस क्रिया को निम्न प्रकार समझा जा सकता है।

- \* p n (GaAs) highly doped, and forward Biased.
- \* Small  $I_F$  current flows as movement of el's and holes.
- \* el's and holes recombination give rise to photon.
- \* This photon either absorb by el's in V.B and raise this el's to C.B or some stimulate already exist el's in C.B.
- \* When forward current value  $I_F$  is raised more then their is more recombination so more photons is generated randomly and absorb by el's in V.B. This give rise to el's to come to C.B. i.e population Inversion is achieved.
- \* Now emitted photon, stimulate el's in C.B to fall back to V.B and release energy ( $C.B - V.B = E_g$ ) in form of photon.
- \* Such photon has equal phase as of incident photon.
- \* This process happens repeatedly and LASER action started.

advantages of LED ① Small size ② Easy Modulation by  $I_F$   
③ Easy construction ④ cost is less.